



APTM50UM19SG Information

Heisener.com

Part Number APTM50UM19SG
Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 163A J3

Package J3 Module

For the pricing/inventory/lead time, please contact

us

For Reference Only

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APTM50UM19SG Specifications

Manufacturer Part NumberAPTM50UM19SGManufacturerMicrosemi CorporationCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageJ3 ModuleSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C163ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 10mAGate Charge (Qg) (Max) @ Vgs492nC @ 10VInput Capacitance (Ciss) (Max) @ Vds22400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1136W (Tc)Rds On (Max) @ Id, Vgs19 mOhm @ 81.5A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageModulePackage / CaseJ3 ModuleReport errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package J3 Module Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature 40°C ~ 150°C (TJ) Mounting Type Supplier Device Package Module Package / Case J3 Module	Manufacturer Part Number	APTM50UM19SG
Package J3 Module Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Manufacturer	Microsemi Corporation
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Series - N-Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case 1500 Module		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 163A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature 40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case James And Module	Package	J3 Module
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Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case 163A 10V 10V 10V 10W 240mA 492nC @ 10V 22400pF @ 25V 23400pF @ 25V 25400pF @ 25V 136W (Tc) 1136W (Tc) 1136W (Tc) Chassis Mount Module Package / Case J3 Module	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature Auo°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case J3 Module	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case J3 Module	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id 5V @ 10mA Gate Charge (Qg) (Max) @ Vgs 492nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Current - Continuous Drain (Id) @ 25°C	163A
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 22400pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Vgs(th) (Max) @ Id	5V @ 10mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)1136W (Tc)Rds On (Max) @ Id, Vgs19 mOhm @ 81.5A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageModulePackage / CaseJ3 Module	Gate Charge (Qg) (Max) @ Vgs	492nC @ 10V
FET Feature - Power Dissipation (Max) 1136W (Tc) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Input Capacitance (Ciss) (Max) @ Vds	22400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19 mOhm @ 81.5A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs19 mOhm @ 81.5A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageModulePackage / CaseJ3 Module	FET Feature	-
Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Power Dissipation (Max)	1136W (Tc)
Mounting Type Chassis Mount Supplier Device Package Module Package / Case J3 Module	Rds On (Max) @ Id, Vgs	19 mOhm @ 81.5A, 10V
Supplier Device Package Module Package / Case J3 Module	Operating Temperature	-40°C ~ 150°C (TJ)
Package / Case J3 Module	Mounting Type	Chassis Mount
	Supplier Device Package	Module
Report errors?	Package / Case	J3 Module
		Report errors?

APTM50UM19SG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APTM50UM19SG Payment Methods



















APTM50UM19SG Shipping Methods













If you have any question about APTM50UM19SG, please do not hesitate to contact us!

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